

FDN361AN

N-Channel, Logic Level, PowerTrench™

General Description

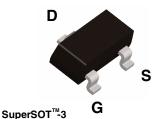
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

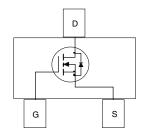
Applications

- DC/DC converter
- Load switch
- Motor drives

Features

- 1.8 A, 30 V. $R_{DS(on)} = 0.100~\Omega~$ @ $V_{GS} = 10~V$ $R_{DS(on)} = 0.150~\Omega~$ @ $V_{GS} = 4.5~V.$
- Low gate charge (2.1nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R_{DS(on)}.
- High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	FDN361AN	Units	
V_{DSS}	Drain-Source Voltage	30	V	
V _{GSS}	Gate-Source Voltage - Continuous	<u>±</u> 20	V	
I _D	Drain Current - Continuous	(Note 1a)	1.8	Α
	- Pulsed		8	
P _D	Power Dissipation for Single Operation	0.5	W	
		(Note 1b)	0.46	
T _J , T _{sta}	Operating and Storage Junction Temperat	-55 to +150	°C	

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device Marking Device		Tape width	Quantity
361	361 FDN361AN		8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Cha	racteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V	
∆BVdss ∆Tj	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		24		mV/∘C	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μ A	
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA	
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
On Char	acteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.8	3	V	
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		-4.2		mV/∘C	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 1.4 \text{ A}$		0.072 0.107 0.105	0.1 0.16 0.15	Ω	
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	8			Α	
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 1.8 A		5		S	
Dynamic	c Characteristics						
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$		220		pF	
Coss	Output Capacitance			50		pF	
C _{rss}	Reverse Transfer Capacitance	1		20		pF	
Switchin	ng Characteristics (Note 2)						
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		3	6	ns	
t	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6.0 \Omega$		11	22	ns	
$t_{\text{d(off)}}$	Turn-Off Delay Time	7		7	14	ns	
t _f	Turn-Off Fall Time			3	6	ns	
Qg	Total Gate Charge	V _{DS} = 15 V, I _D = 1.8 A,		2.1	4	nC	
Q _{gs}	Gate-Source Charge	V _{GS} = 5 V		0.8		nC	
Q_{gd}	Gate-Drain Charge	7		0.7		nC	
Drain-Sc	ource Diode Characteristics	and Maximum Ratings					
I _S	Maximum Continuous Drain-Source			1	0.42	Α	
٥.	Maximum Continuous Diam-Coun	DO DIOGO I OIWAIA OAIIOIR	1	1	J U Z	, , ,	

V_{SD}

 R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.

 $V_{GS} = 0 \text{ V}, I_S = 0.42 \text{ A}$ (Note 2)



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. Cu.

Drain-Source Diode Forward



b) 270°C/W when mounted on a mininum pad.

Scale 1 : 1 on letter size paper

Voltage

2. Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

0.75

1.2

Typical Characteristics (continued)

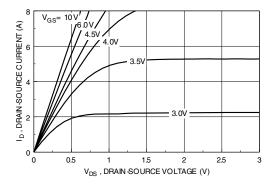


Figure 1. On-Region Characteristics.

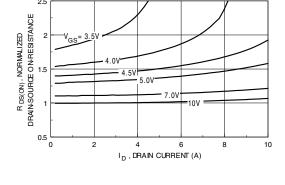


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

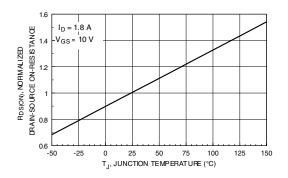


Figure 3. On-Resistance Variation with Temperature.

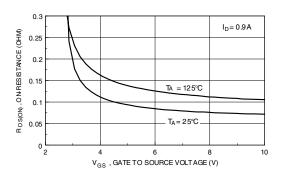


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

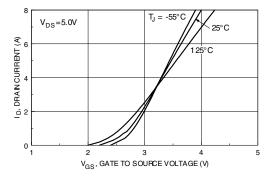


Figure 5. Transfer Characteristics.

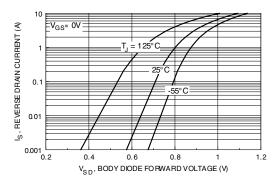
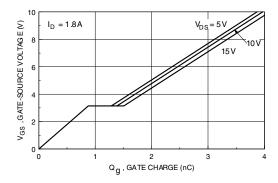


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



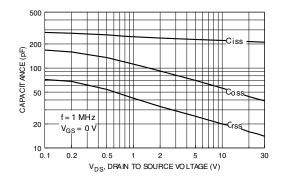
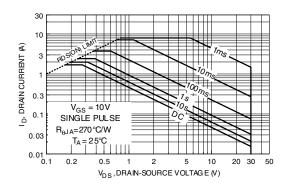


Figure 7. Gate-Charge Characteristics.





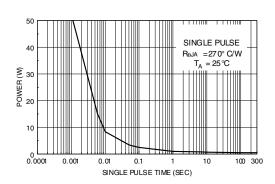


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

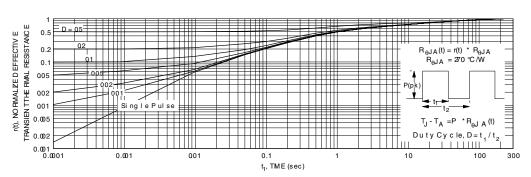
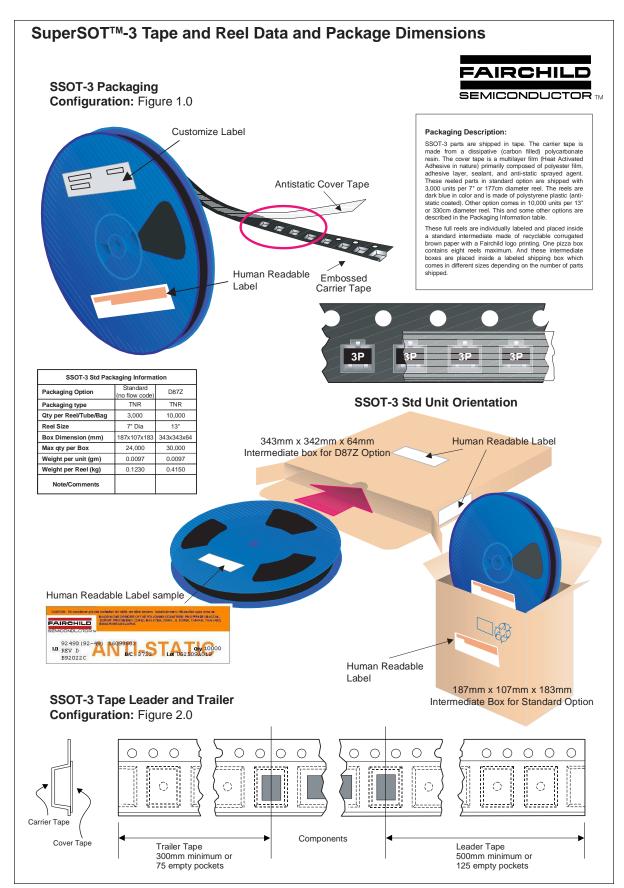


Figure 11. Transient Thermal Response Curve.

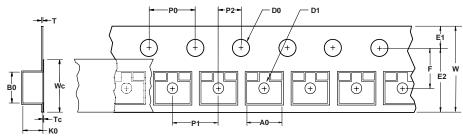
Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.

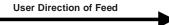




SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



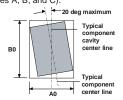


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

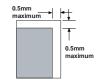
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

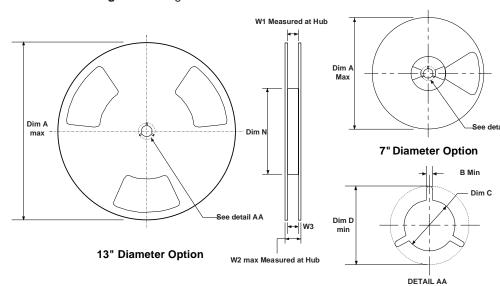


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

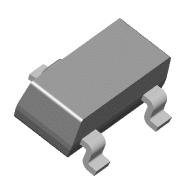
SSOT-3 Reel Configuration: Figure 4.0

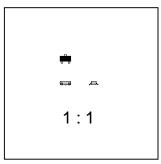


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

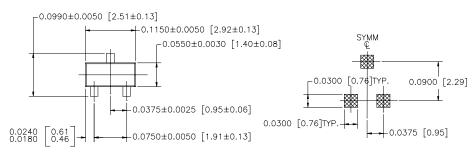
SuperSOT™-3 (FS PKG Code 32)



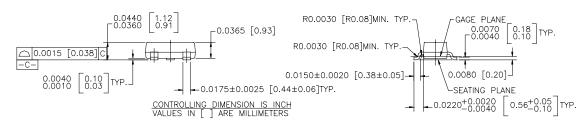


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT™ QFET™ FACT Quiet Series™ QS™

FAST®Quiet Series $^{\text{TM}}$ FASTr $^{\text{TM}}$ SuperSOT $^{\text{TM}}$ GTO $^{\text{TM}}$ SuperSOT $^{\text{TM}}$ HiSeC $^{\text{TM}}$ SuperSOT $^{\text{TM}}$

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.